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## Multilayered structures $\text{InSb}_{1-x}\text{Bi}_x/\text{InSb}$ -materials for infrared photodetectors

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In the work investigations of electron energy spectrum dependence from thickness ( $l$ ) and number ( $N$ ) of layers are carried out as well as treating with rays process in 5-11 layer heterostructures  $\text{InSb}_{0.97}\text{Bi}_{0.03}/\text{InSb}$  is considered by  $k$ - $p$ - and matrix methods. Calculations verified by experiments<sup>[1]</sup> show that with an addition of every pair of layers (well/barrier) there is an energy level appearance.  $N$ -increasing leads to spectrum displacement into the NIR-field. For thick ( $l > 0.1$   $\mu\text{m}$ ) layers it's typical high NIR-sensitivity.

Because of the continuity of electromagnetic field tangential constituents at the heteroboundary the transfer matrix  $Z$  is single. Through the all multilayer structure  $Z$  is the product of  $Z_i$  through  $N_i$  layers beginning at the side of illumination. With  $N$ -increasing there is a rise of the superlattice reflection coefficient  $R$ . When  $N=11$ ,  $R \rightarrow 1$ , i. e. structure is almost an ideal reflective coating (illumination angle  $\alpha=0$ ,  $\lambda=7.7$  and  $11$   $\mu\text{m}$ ,  $l=0.1$   $\mu\text{m}$ ). For  $\alpha=0$  there is a transparency maximum. If  $N=3$ , the transparency coefficient  $P \rightarrow 0.8$ , with  $N$ -increasing up to  $17P$  decreases to  $0.3$ . When  $\alpha=0-\pi/2$ ,  $P=0.8-0$ . So varying illumination angle one can obtain required  $P$  and  $R$  without changing of multilayer structure configuration.

Superlattice properties can be used in infrared photodetectors, clarified coatings, heterojunction smoothing to avoid degradation of frequency characteristics and Q-factor because of the energy band gaps in sharp heterojunctions.

### References

- [1] L. S. Lunin, M. L. Lunina, A. V. Blagin Avalanche photodiodes on the base of  $\text{InSbBi-InSb}$  superlattice. /Proc. Of VII International conference "Actual problems of solid state electronics and microelectronics". Divnomorskoe, Russia, 2000, V.2. P.172.